PMEG2010EH; PMEG2010EJ; PMEG2010ET

1 A very low V_F MEGA Schottky barrier rectifiers

Rev. 04 — 20 March 2007

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			Configuration
	NXP	JEITA	JEDEC	
PMEG2010EH	SOD123F	-	-	single
PMEG2010EJ	SOD323F	SC-90	-	single
PMEG2010ET	SOT23	-	TO-236AB	single

1.2 Features

Forward current: I_F ≤ 1 A

Reverse voltage: V_R ≤ 20 V

Very low forward voltage

Small SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	1	Α
V_R	reverse voltage		-	-	20	V
V _F	forward voltage	$I_F = 1000 \text{ mA}$	<u>[1]</u> _	420	500	mV

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 3. Pinning

Table 3. I	iii		
Pin	Description	Simplified outline	Symbol
SOD123F; S	OD323F		
1	cathode	<u>[1]</u>	54
2	anode	001aab540	1 2 2 sym001
SOT23			
1	anode		_
2	n.c.	3	3
3	cathode	1 2	1 2 n.c. 006aaa436

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
PMEG2010EH	-	plastic surface-mounted package; 2 leads	SOD123F	
PMEG2010EJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F	
PMEG2010ET	-	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG2010EH	A9
PMEG2010EJ	AH
PMEG2010ET	*AU

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	20	V
l _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	1	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$			
	PMEG2010EH		-	7	Α
	PMEG2010EJ		-	7	Α
	PMEG2010ET		-	5	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	-	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG2010EH		<u>[1]</u> _	375	mW
			[2] _	830	mW
	PMEG2010EJ		[1] _	350	mW
			[2] _	830	mW
	PMEG2010ET		[1] _	280	mW
			[2] _	420	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 7. Thermal characteristics

Table 1.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG2010EH		[2] _	-	330	K/W
			[3]	-	150	K/W
	PMEG2010EJ		[2] _	-	350	K/W
			[3]	-	150	K/W
	PMEG2010ET		[2] _	-	440	K/W
			[3] _	-	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[4]</u>			
	PMEG2010EH		-	-	60	K/W
	PMEG2010EJ		-	-	55	K/W
	PMEG2010ET		-	-	120	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

7. Characteristics

 Table 8.
 Characteristics

 T_{amb} = 25 °C unless otherwise specified.

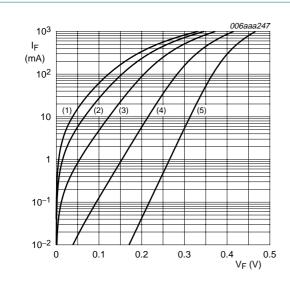
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	90	130	mV
		$I_F = 1 \text{ mA}$	-	150	190	mV
		$I_F = 10 \text{ mA}$	-	210	240	mV
		$I_F = 100 \text{ mA}$	-	280	330	mV
		$I_F = 500 \text{ mA}$	-	355	390	mV
		$I_F = 1000 \text{ mA}$	-	420	500	mV
I _R	reverse current	V _R = 10 V	-	15	40	μΑ
		$V_{R} = 20 \text{ V}$	-	40	200	μΑ
C_d	diode capacitance	$V_R = 1 V;$ f = 1 MHz	-	66	80	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

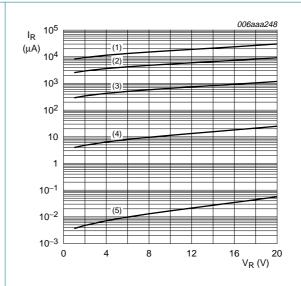
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[4] Soldering point of cathode tab.



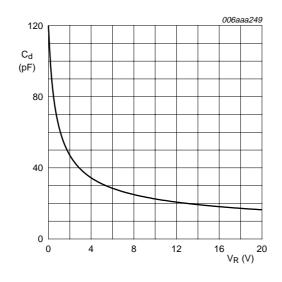
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \,^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

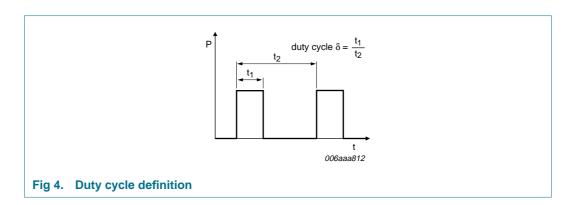


f = 1 MHz; T_{amb} = 25 °C

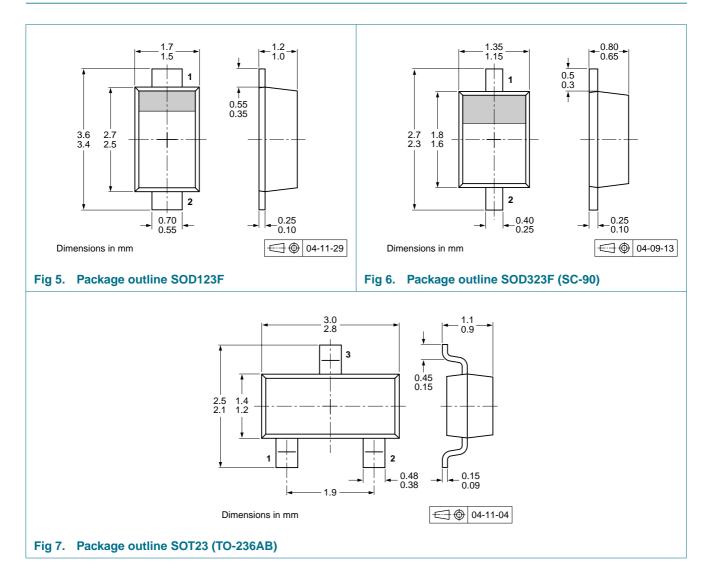
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Test information



9. Package outline



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10. Packing information

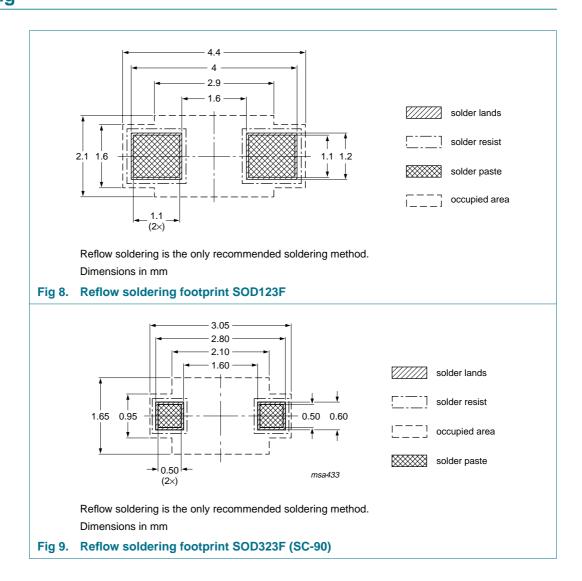
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing		quantity	
			3000	10000	
PMEG2010EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG2010EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135	
PMEG2010ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

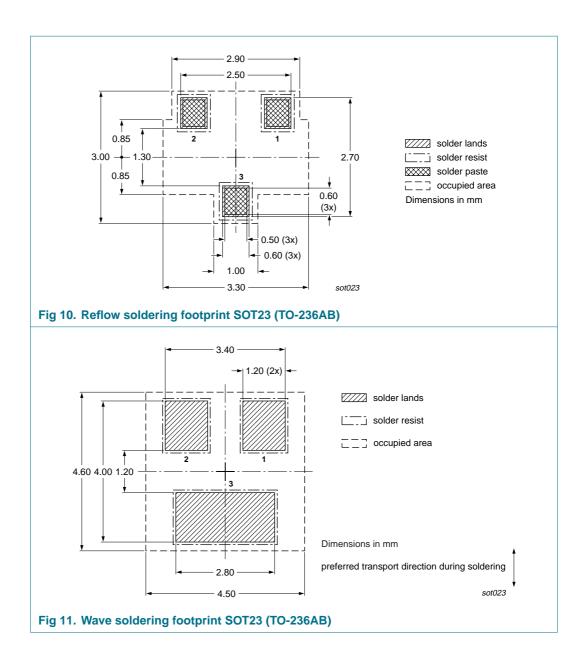
^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 10. Revision history

,	•				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMEG2010EH_EJ_ET_4	20070320	Product data sheet	-	PMEGXX10EH_EJ_SER_3	
Modifications:		of this data sheet has be of NXP Semiconductors.	en redesigned to com	ply with the new identity	
	 Legal texts 	have been adapted to th	e new company name	where appropriate.	
		ers PMEG2010EH and P 0EH_EJ_SER_3	MEG2010EJ separate	ed from data sheet	
	 Type numb 	er PMEG2010ET added			
	Section 1.1 "General description": amended				
	 Section 1.2 	"Features": amended			
	Section 1.3	"Applications": amended	i		
	 Section 8 " 	Test information": added			
	• Figure 7, 1	<u>0</u> and <u>11</u> : added			
	Section 13	"Legal information": upda	ated		
PMEGXX10EH_EJ_SER_3	20050411	Product data sheet	-	PMEGXX10EJ_SER_2	
PMEGXX10EJ_SER_2	20050131	Product data sheet	-	PMEGXX10EJ_SER_1	
PMEGXX10EJ_SER_1	20040907	Objective data sheet	-	-	

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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